

# H-Sensors and Fusion Work at SNL-CA

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Thomas Lemp and Thomas Friedman (SNL-NM)



Useful discussions with Peter Stangeby (Univ. of Toronto)  
And Bob Bastasz (SNL-CA retired)

## Outline

Overview of Hydrogen Work  
Details of Fusion Program on PSI  
Motivation for Atomic Hydrogen Measurements  
Pd-MOS Hydrogen Sensors

Tritium Focus Group Meeting, INL, September 23-25, 2014



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# Building a science-based understanding of hydrogen (and helium) behavior in materials

## ■ High pressure hydrogen storage for Gas Transfer Systems and hydrogen / fuel cell industry →

- Embrittlement, permeation, trapping, microstructural effects, corrosion, Codes and Standards (H<sup>2</sup> safety)

## ■ Metal hydride studies for hydrogen storage →

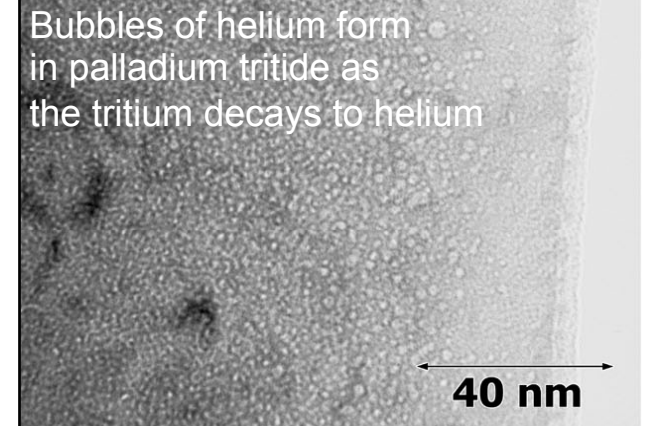
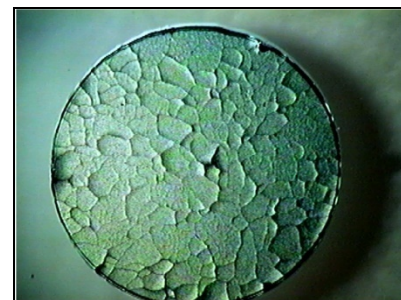
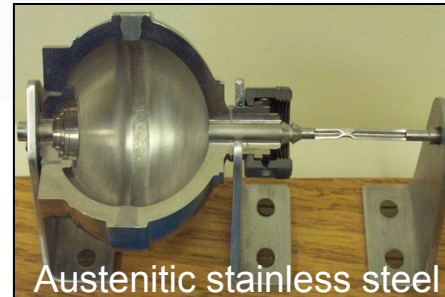
- He trapping from T decay, film adhesion, aging, new materials

## ■ Tritium production (TPBAR) →

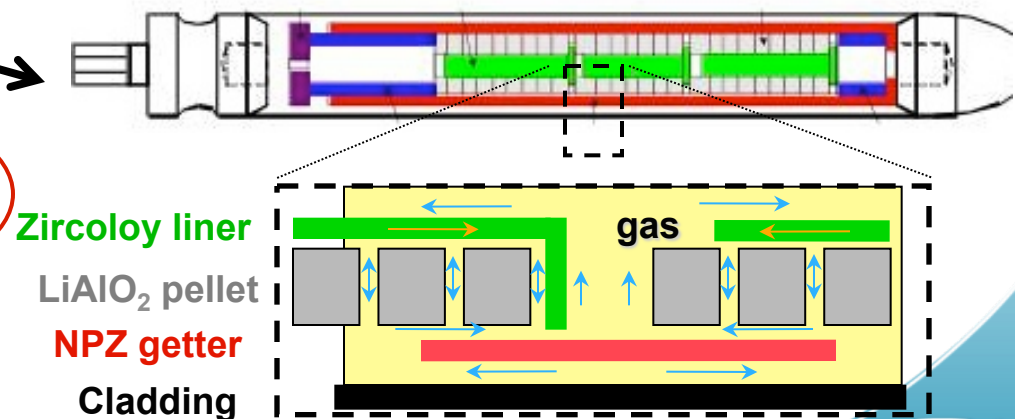
- T migration in a complex materials environment

## ■ Plasma-surface interactions (PSI) studies needed for magnetic fusion energy

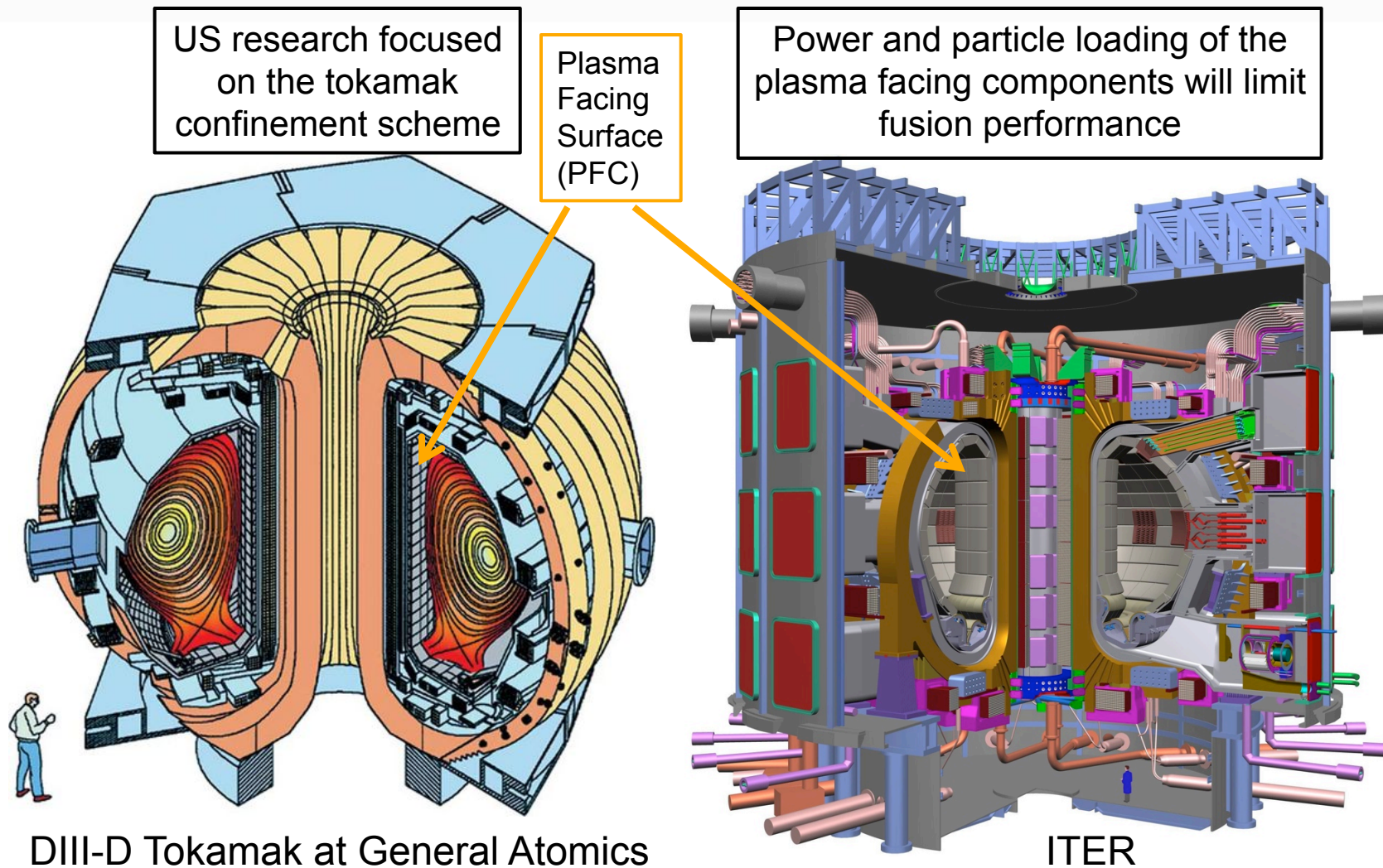
R&D efforts span a number of applied programs at SNL-CA



## Tritium Producing Burnable Absorber Rods



# Magnetic fusion energy research

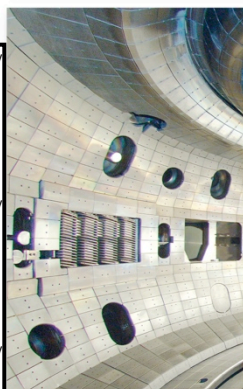
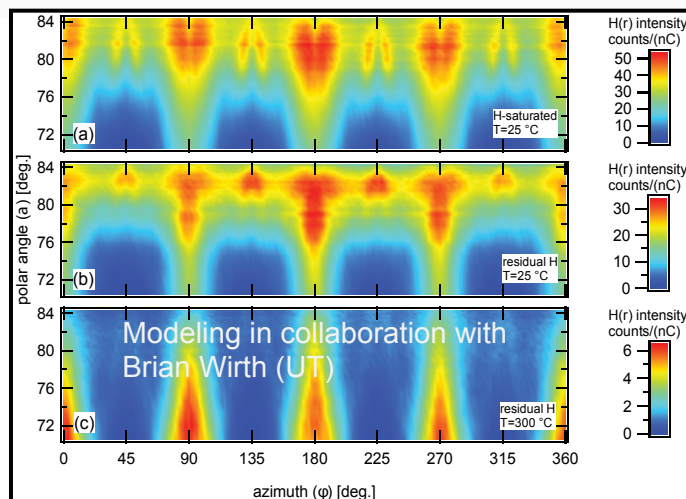


Greenwald report, ReNeW study, and OFES all agree on importance of PSI/PFC

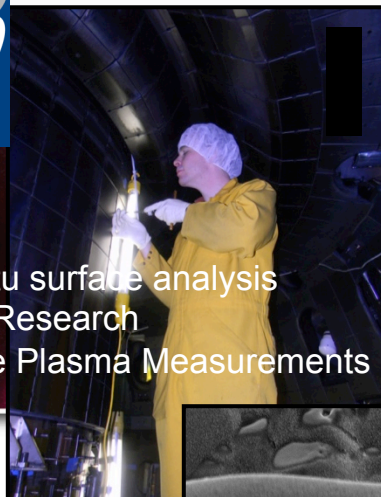


# SNL-CA PSI Science Center Research (FY10-14)

Fundamental surface science of  
H effects in ARIES



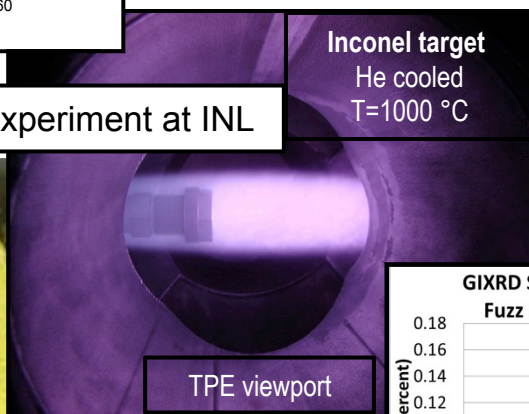
In-situ surface analysis  
PSI Research  
Edge Plasma Measurements



Tritium Plasma Experiment at INL

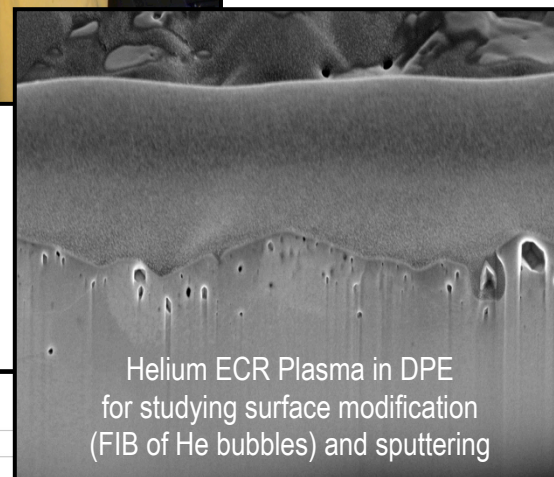
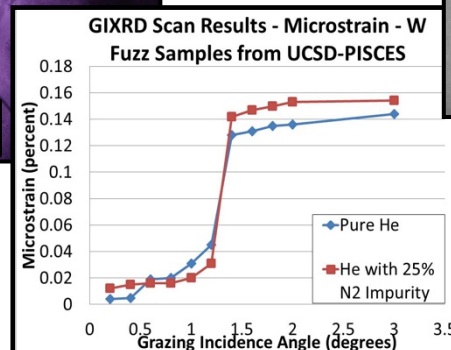


Sandians at TPE

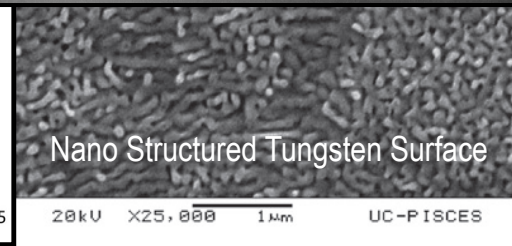


Inconel target  
He cooled  
T=1000 °C

TPE viewport



Helium ECR Plasma in DPE  
for studying surface modification  
(FIB of He bubbles) and sputtering



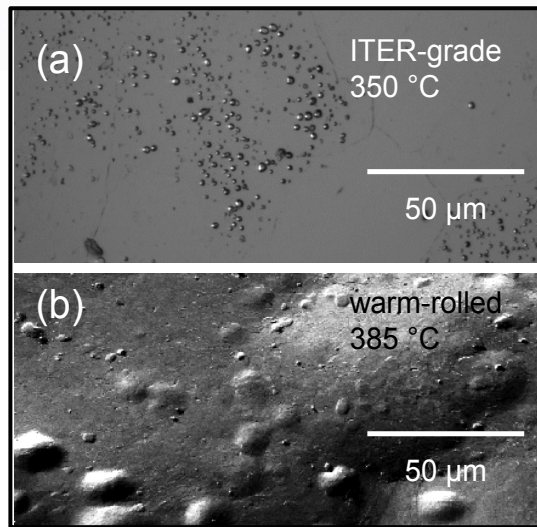
Nano Structured Tungsten Surface

**The PSI SC efforts are heavily leveraged with our base program funding**

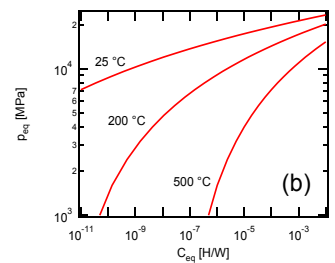
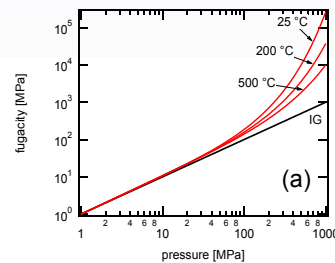




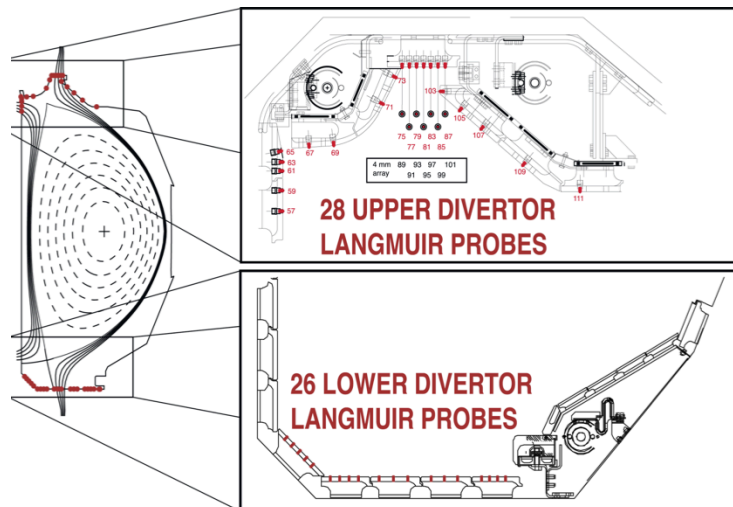
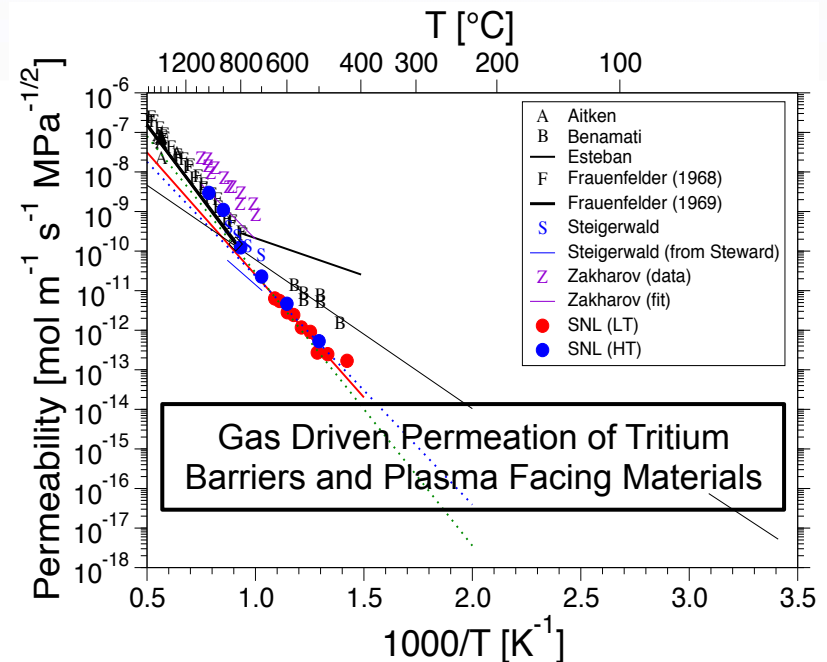
# SNL-CA base program (Technology & DIII-D)



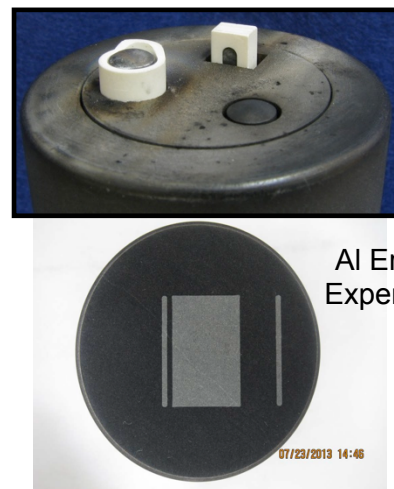
Hydrogen induced blistering of W



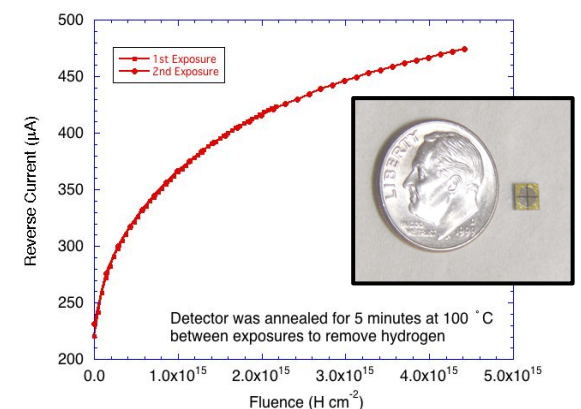
Equilibrium Pressure From Bubble Model



Edge Plasma Characterization in DIII-D



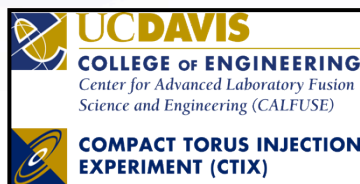
Plasma Measurements and Erosion/Redeposition Experiments on DiMES (DIII-D)



Hydrogen Microsensor Development

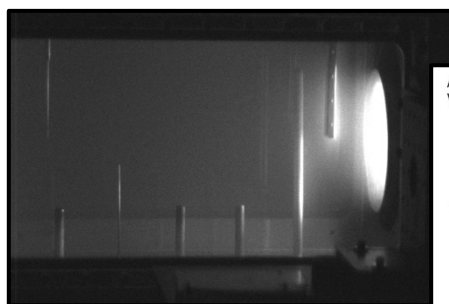


# Other fusion research at SNL-CA

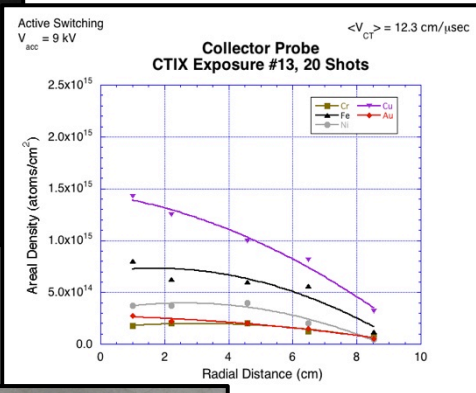


## Plasma Surface Interactions in the Compact Toroid Injection Experiment (started in FY10)

### Impurities Exiting the Plasma Accelerator



Collector Probes in CTIX



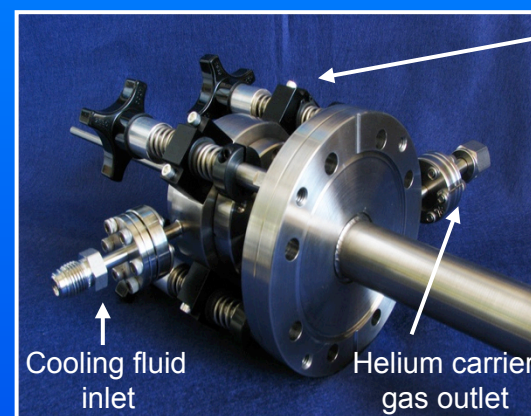
Improved Electrode Design

Plasma Sprayed Tungsten For Improved Performance

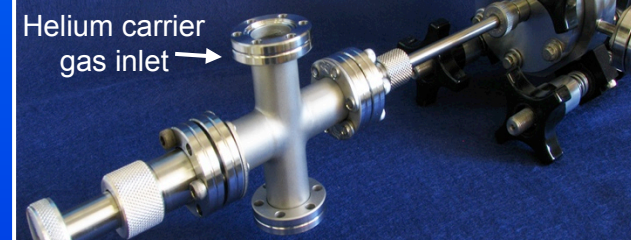


Final weld alignment

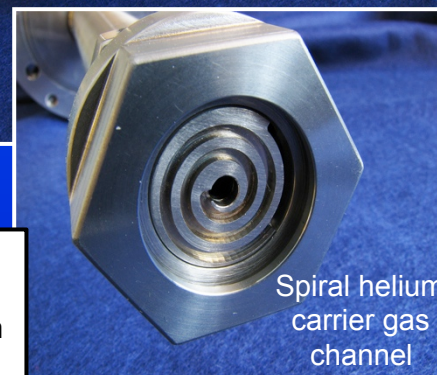
## Membrane Holder Photos



Development of Plasma driven Permeation holder for TPE



US-Japan Collaboration on PFC evaluation by Tritium Plasma, Heat, and Neutron Irradiation eXperiments



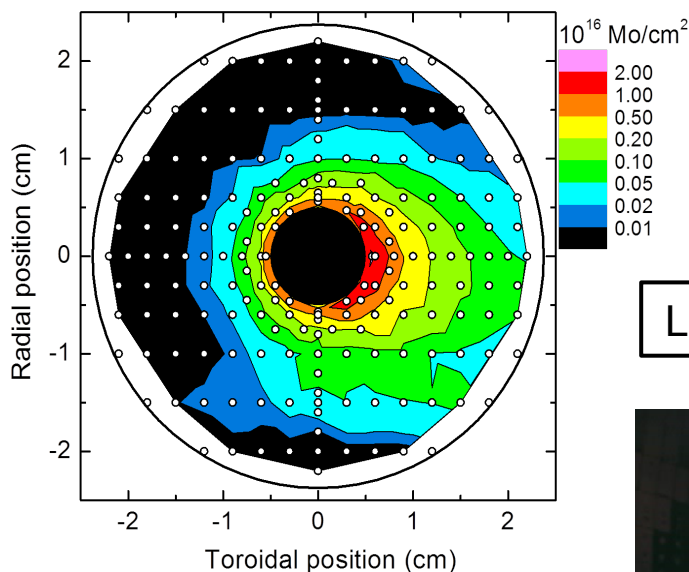


# Sandia Ion Beam Laboratory (NM)



DiMES experiments on DIII-D

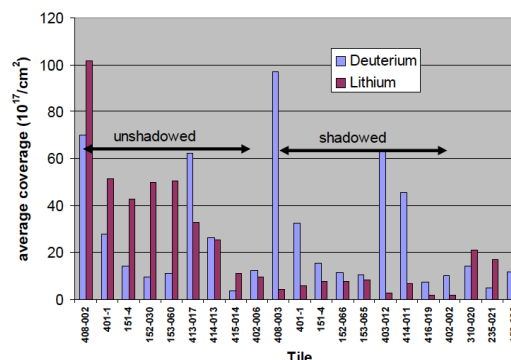
**Molybdenum**  
erosion 0.5 nm/s



19% redeposited locally  
with  $\lambda=2.3$  mm

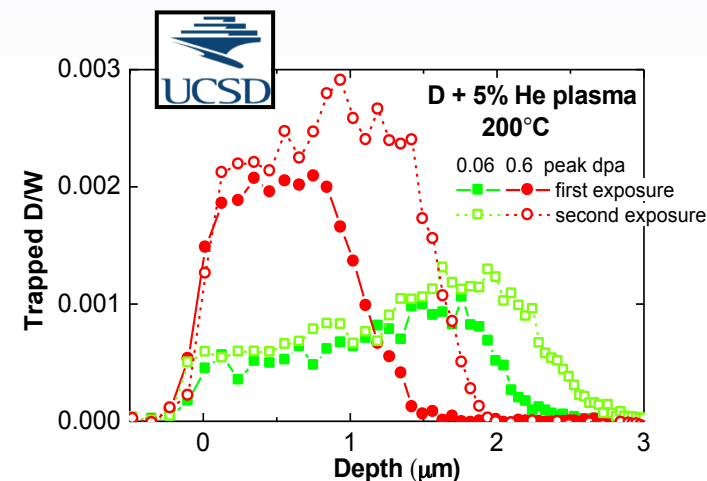


Average coverage of Li & D on each tile



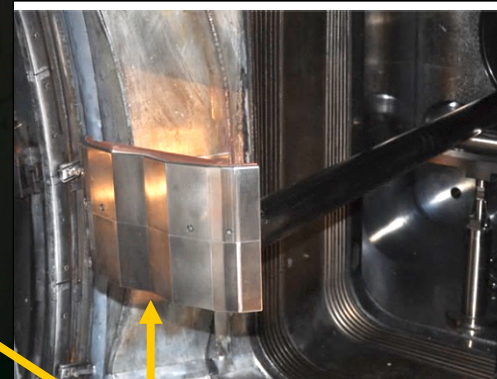
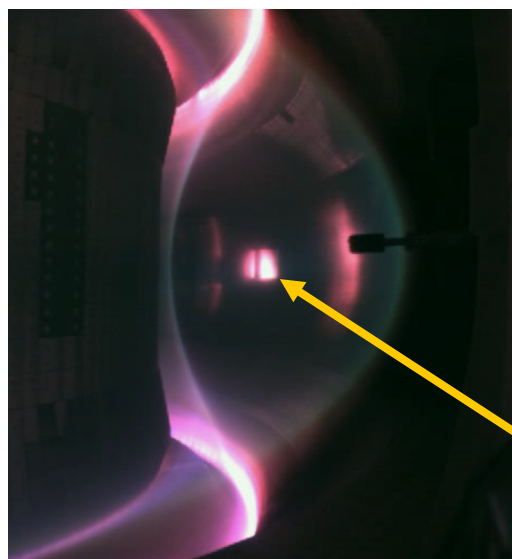
Tiles in Li shadow have ~ 10x less Li than unshadowed tiles, whereas D coverage is similar.

Li and D coverage on NSTX tiles



Deuterium trapping studies on  
damaged tungsten in PISCES

EAST/MAPES Material Erosion Experiment



**MAPES**



# US fusion program has a major focus studying plasma-material interactions (including erosion)

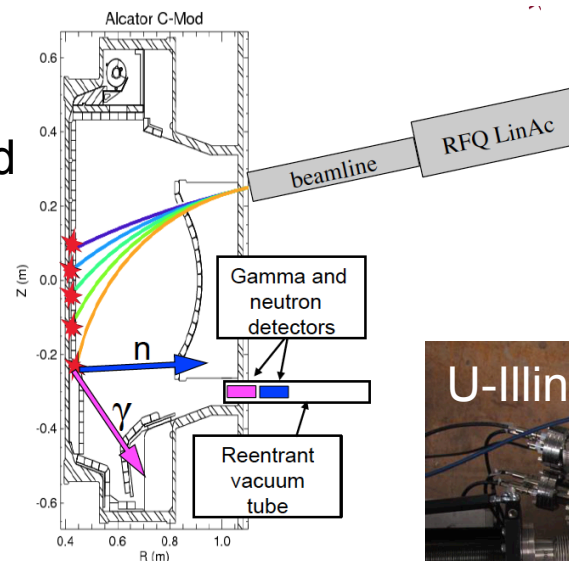
## ■ DIII-D

- DiMES (divertor) and MiMES (first wall) experiments provide erosion / redeposition data for plasma-material interaction model validation (REDEP/ WBC-ITMC code)



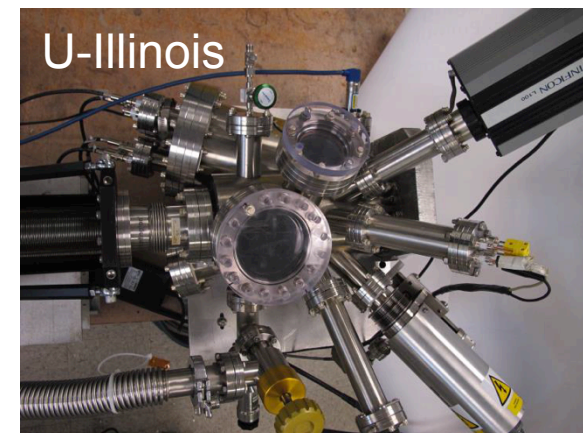
## ■ Alcator C-Mod

- High Z erosion and redeposition studied using a dedicated ion beam facility
- AIMS: Accelerator-based In-situ Materials Surveillance (compact RFQ LinAc injects 0.9 MeV D<sup>+</sup>)



## ■ NSTX-U

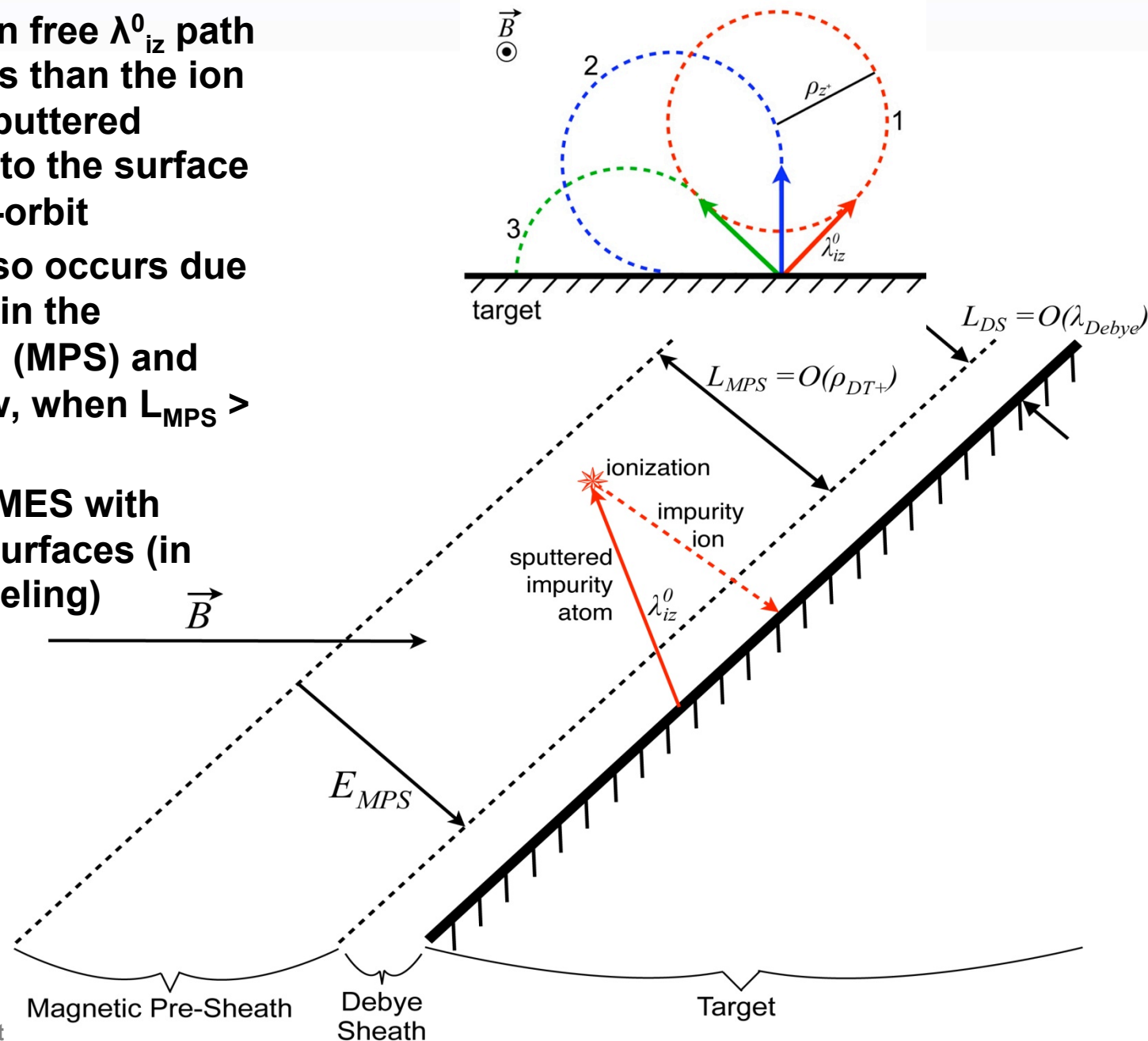
- MAPP: Material Analysis and Particle Probe (sample exposure with in-situ TDS, XPS, LEISS, DRS)



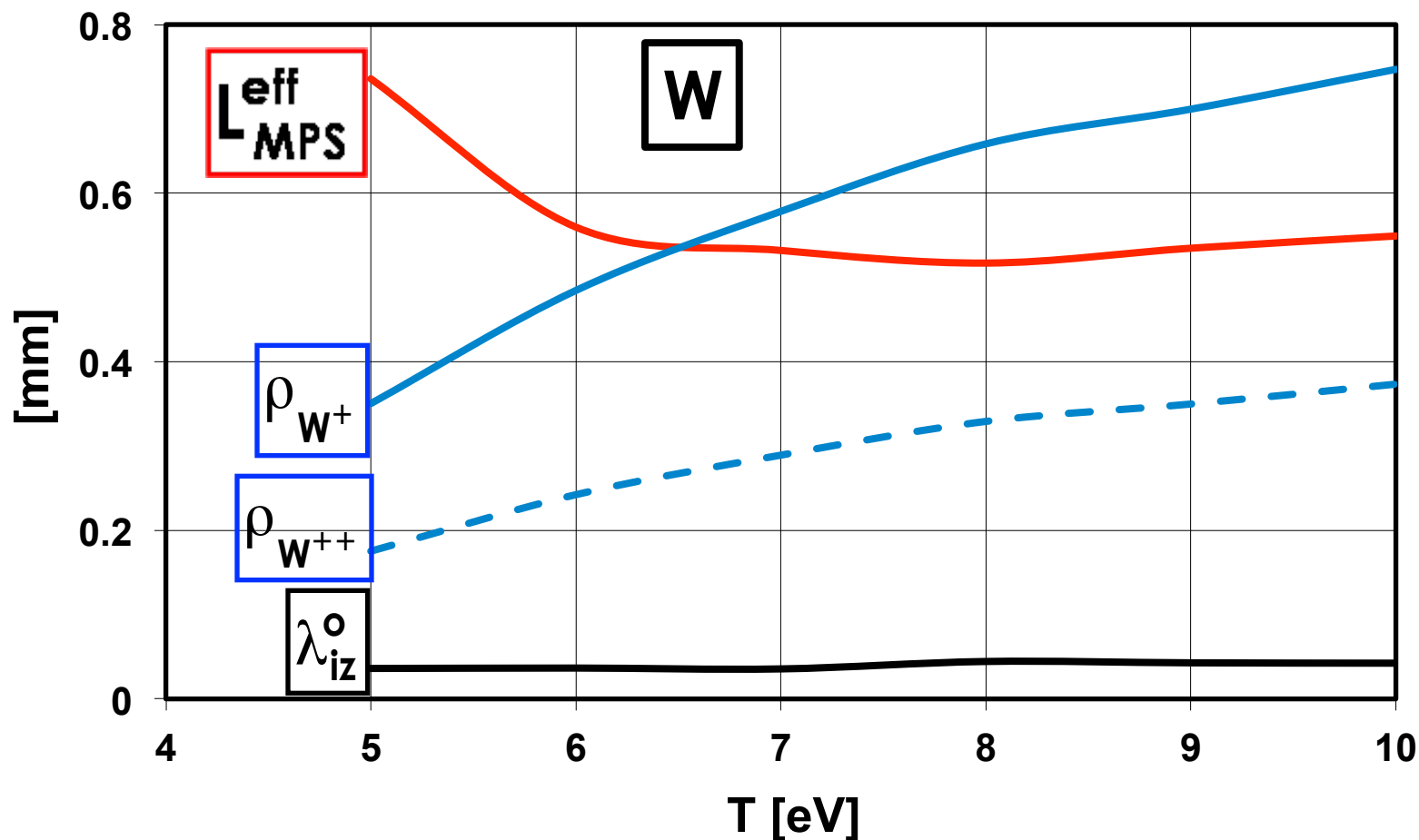


# Prompt redeposition in the magnetized sheath of the divertor is expected to reduce net erosion

- If the ionization mean free  $\lambda_{iz}^0$  path is comparable or less than the ion Larmor radius  $\rho_{z+}$ , sputtered impurity ions return to the surface during the first gyro-orbit
- Fast redeposition also occurs due to the strong E-field in the magnetic pre-sheath (MPS) and friction with fast flow, when  $L_{MPS} > \lambda_{iz}^0$
- Demonstrated on DiMES with tungsten and moly surfaces (in agreement with modeling)



For tungsten, prompt deposition should be effective in DT devices via both strong MPS forces and large  $\rho_W$



ITER case with  $n_e = 10^{21} \text{ m}^{-3}$ ,  $B = 5 \text{ T}$

Courtesy of P. Stangeby



# Prompt deposition *is not* expected at the first wall

- Much lower far scrape off layer (SOL) plasma density ( $\sim \times 10^{-3}$ ) will result in longer ionization mean free path  $\lambda_i^0$ 
  - Sputtered wall neutrals will penetrate into the far SOL and experience migration towards the divertor
- The sputtering can be due to either plasma ions or charge exchange (c-x) neutrals
- While several efforts to characterize the first wall c-x flux occurred during the 80's / 90's, no current investigations exist on US tokamaks
  - LENA (Low Energy Neutral Analyzer): PLT, ASDEX, Alcator C-Mod (installed only)
  - CRP (Carbon Resistance Probe): TMX-U, PLT, ASDEX, TFTR
  - Pd-MOS H-sensors (Palladium Metal-Oxide-Semiconductor)
    - ◆ Diode type: ZT-40M and TFTR
    - ◆ Capacitance type: DIII-D, NSTX
- Is the flux of c-x neutrals important in FW erosion? What is the poloidal and toroidal distribution of the c-x flux? How will c-x induced erosion scale in future devices?
- Simple estimate on next viewgraph: physical sputtering of T using  $E=300$  eV (Eckstein 2002), normal incidence yield doubled to account for surface roughness, no sputtering by other plasma or wall species,  $P_{cx} = 0.05 P_{heat}$  (~Kukushkin for ITER)

# Rough estimate of c-x induced FW erosion

| For 300 eV<br>T° c-x<br>sputtering<br>of walls | P <sub>heat</sub><br>[MW] | annual<br>run time<br>[s/year] | beryllium<br>net wall<br>erosion<br>rate<br>[kg/yr] | boron<br>net wall<br>erosion<br>rate<br>[kg/yr] | carbon<br>net wall<br>erosion<br>rate<br>[kg/yr] | tungsten<br>net wall<br>erosion<br>rate<br>[kg/yr] |
|--|---------------------------|--------------------------------|---|---|--|--|
| DIII-D   | 20                        | 10 <sup>4</sup>                | 0.13  | 0.11  | 0.08   | 0.16   |
| JT-60SA  | 34                        | 10 <sup>4</sup>                | 0.22  | 0.19  | 0.15   | 0.27   |
| EAST   | 24                        | 10 <sup>5</sup>                | 1.6   | 1.2   | 0.82   | 1.8  |
| ITER   | 100                       | 10 <sup>6</sup>                | 77 [29*]<br>{60***}                                 | 64  | 44 [53*]<br>{54***}                              | 92 [41*]<br>{46***}                                |
| Vulcan   | 20                        | 10 <sup>7</sup>                | 120   | 100   | 70   | 150  |
| FDF  | 100                       | 10 <sup>7</sup>                | 610   | 500   | 340  | 740  |
| Reactor  | 400                       | 2.5x10 <sup>7</sup>            | 6500  | 5300  | 3700   | 7900<br>[5000**]                                   |

\* Kukushkin B2-EIRENE calculation

\*\*Lackner

\*\*\*Behrisch

Courtesy of P. Stangeby



# Techniques for measuring c-x flux

## ■ LENA (Low Energy Neutral Analyzer)

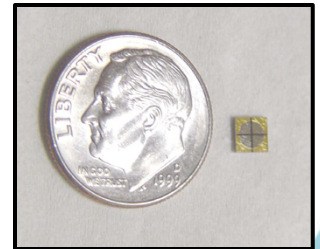
- Pros: provides good time and energy resolution
- Cons: Available at only a few locations (usually one) due to size and complexity

## ■ CRP (Carbon Resistance Probe)

- Pros: compact and low power device, energy discrimination by array with varying overlayers, good time resolution
- Cons: device saturates permanently at  $2 \times 10^{15}$  H/cm<sup>2</sup>

## ■ Pd-MOS H-sensors (Palladium Metal-Oxide-Semiconductor)

- Pros: compact and low power device, energy discrimination by array with varying overlayers, in-situ reset through heating of device
- Cons: dosimetric (shot by shot), lifetime limited by charge trapping



Each device can play a role towards quantifying c-x flux in existing experiments

# Pd-MOS sensor use in confinement experiments

- First use on ZT-40M demonstrated dosemetric effect of sensors

R. Bastasz, J. Nucl. Mater. 162-164 (1989) 587.

- An array sensor was used on TFTR to demonstrate energy resolving c-x measurement

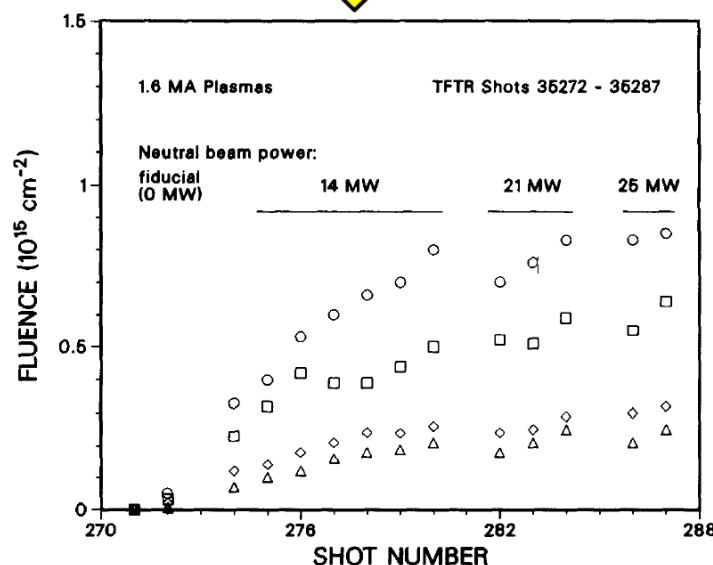
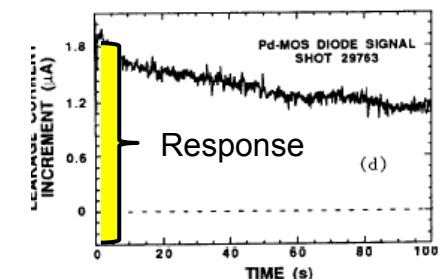
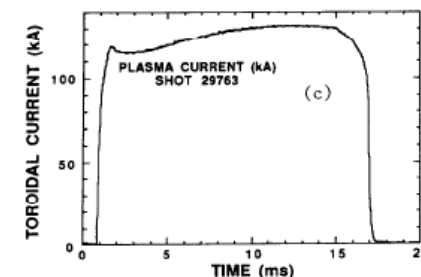
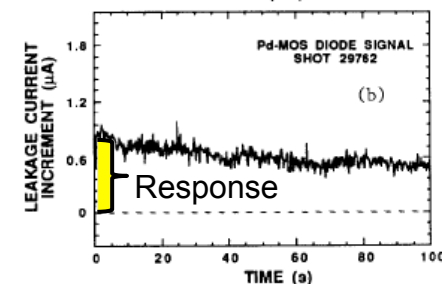
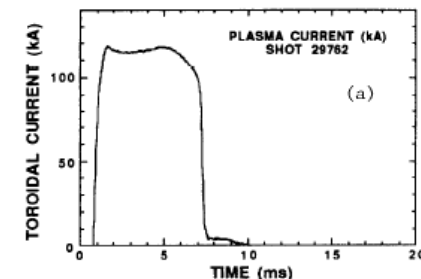
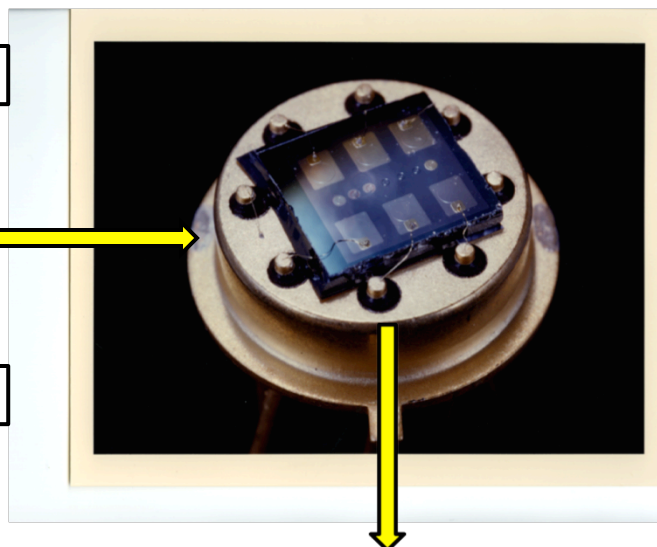
R. Bastasz, J. Nucl. Mater. 176-177 (1990) 1038.

- Switched to capacitance type detectors for easy of fabrication

- Tests on DIII-D and NSTX were not successful

- Likely cause: charge production in thick oxide layer due to x-rays or high energy charged particles

Work by Bob Bastasz and Bob Hughes





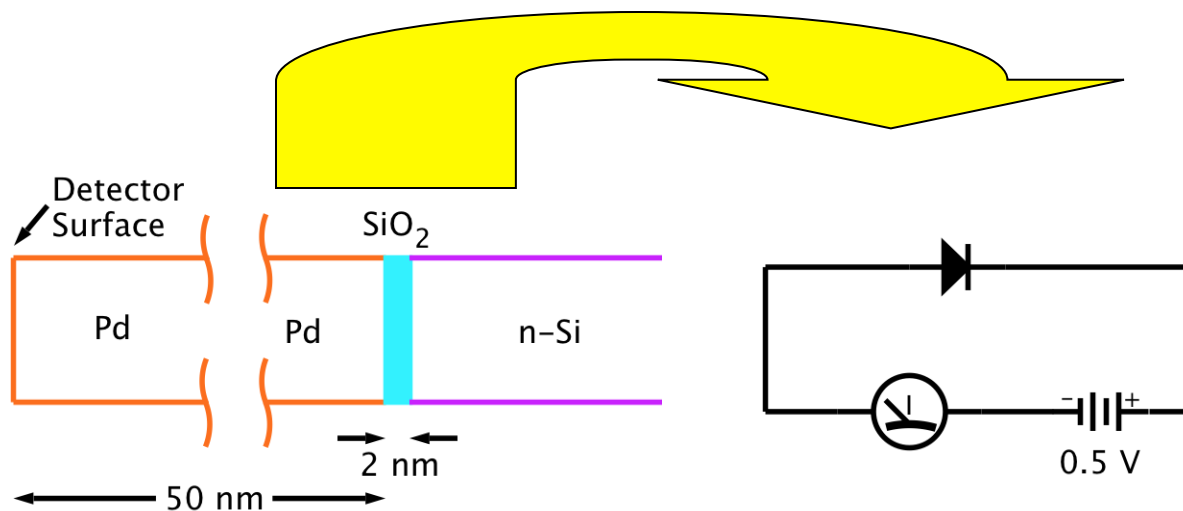
# Pd-MOS Schottky diode type H-sensors

- Diode type detectors will limit charge production due to thin tunnel oxide while a thicker Pd coating can protect from high energy particles
- Hydrogen entering the palladium metal diffuses rapidly, filling surface sites at the Pd-tunnel oxide interface, and changing the barrier height of the diode
  - Simple model of current under reverse bias

$$I_r = AT^2 \exp[-\phi_b / kT]$$

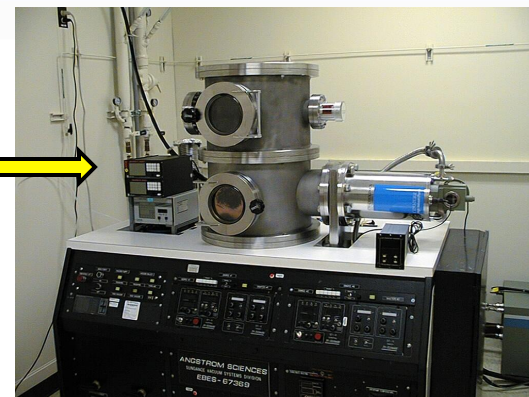
$$\phi_b = \phi_m - \chi$$

- A is a factor depending on the device size and applied voltage, T is the temperature, and  $\phi_b$  is the barrier height.  $\phi_m$  is the metal work function and  $\chi$  is the electron affinity of the silicon. Hydrogen at the interface changes  $\phi_m$  giving a large change in reversed current.

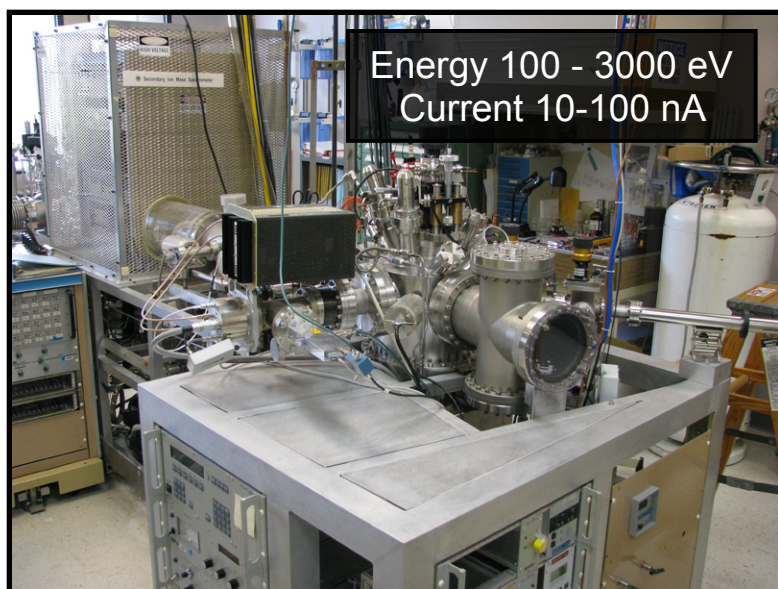


# Initial attempts to fabricate rugged Pd-MOS H-sensors

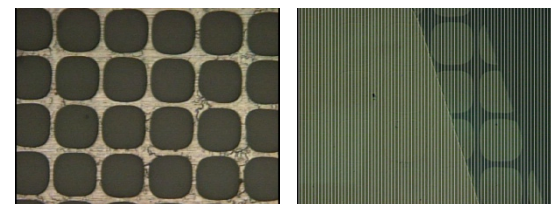
- **Wafers were stripped and 2 nm tunnel oxide grown in the MESAfab (silicon fab at SNL-NM)**
- **Pd films and titanium adhesion grids were deposited at SNL-CA (summer of 2010)**
  - Ti used to improve adhesion in the semiconductor industry
- **Each wafer produced many sensors (3.6 mm square)**
- **Sensors were evaluated using a mass and energy filtered ion beam (SNL-CA)**



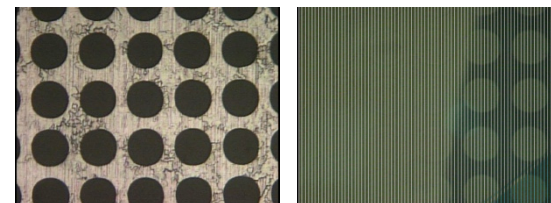
10 keV dual e-beam evaporator used to deposit Pd, Ti, and Au under high vacuum ( $10^{-6}$  Torr). Typical deposition rates are 50 Å/s.



Energy 100 - 3000 eV  
Current 10-100 nA



200 Å thick Ti posts at 200 dots/inch (48% active area) and 2000 Å thick Pd

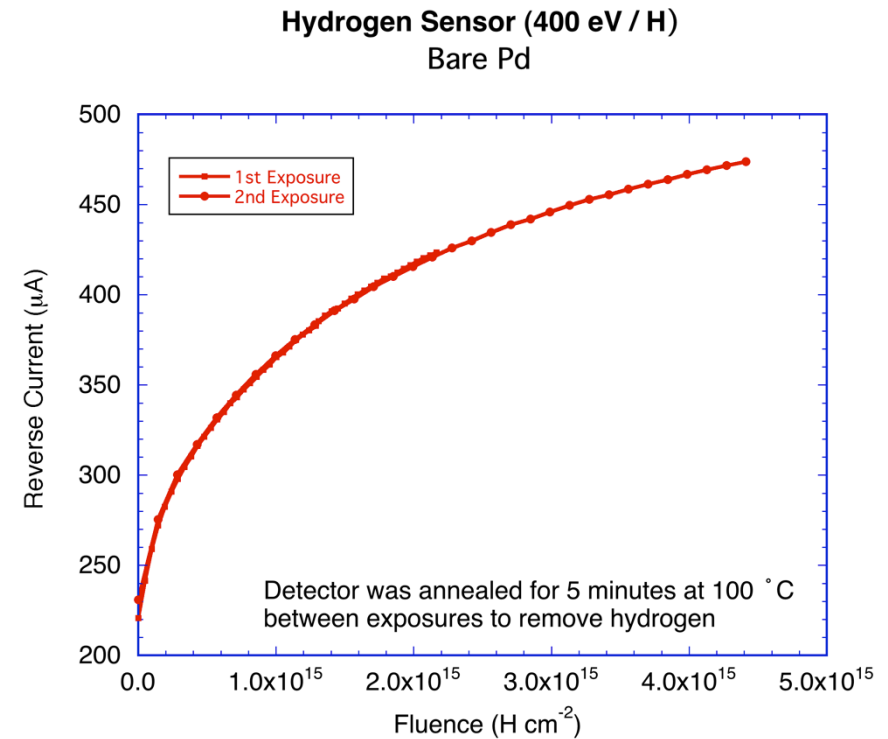


200 Å thick posts at 200 dots/inch (76% active area) and 2000 Å thick Pd



# Ti posts unsuccessful, but diode-type H-sensors did exhibit similar behavior to previous detectors

- 20 nm Ti post array was too reactive and shorted the Pd metal-oxide interface
- Bare Pd sensors exhibited good response and reproducibility. Energy sensitivity needs further study.
- Exploring other options which will exploit extensive processing capabilities at the MESAfab
- Development of rugged detectors will require more than the 2010 several-month effort described here
- Leveraging of the MESAfab facility and expertise would require only a modest investment

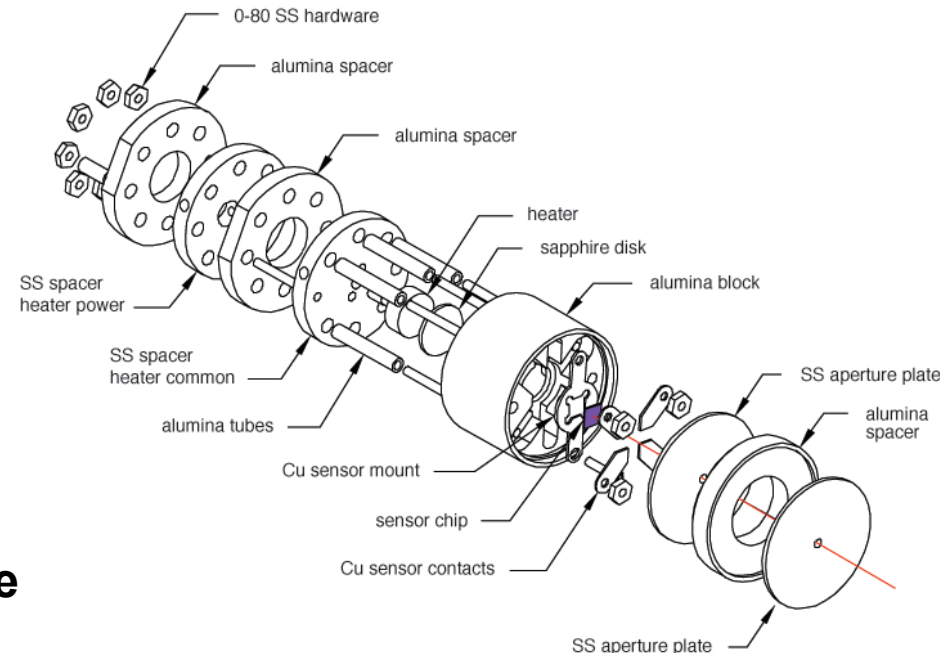


## MESAfab Key Fabrication Capabilities

- |  |  |
|--|--|
| <ul style="list-style-type: none"><li>• Photolithography Processes (Coat/Expose/Develop)</li><li>• Electron Beam (E-Beam) Lithography</li><li>• Reactive Ion Etch</li><li>• Wet Etch/Clean</li><li>• Oxidation and Diffusion</li><li>• Thin Films</li><li>• Chemical Mechanical Polishing (CMP) for planarization</li><li>• Ion Implantation</li><li>• Metrology</li><li>• Deep Reactive Ion Etch (DRIE)</li></ul> | <ul style="list-style-type: none"><li>• Electroplating</li><li>• Packaging</li><li>• MEMS Release</li><li>• Yield Learning</li><li>• Statistical Process Control</li><li>• III-V Compound Semiconductor Epitaxial Growth</li><li>• Mixed-Technology Integration and Processing</li><li>• 3D Integration</li><li>• Materials Characterization</li><li>• Failure Analysis</li><li>• Wafer Bonding and Thinning</li></ul> |
|--|--|

# Summary

- Unlike the divertor, the first wall of tokamaks will not experience prompt redeposition of sputtered material. Thus net erosion will be  $\sim$  gross erosion.
- Simple estimates and more complete simulations indicate that charge-exchange sputtering will result in large migration of first wall material in future devices.
- The development of Pd-MOS diode H-sensors would provide a tool that could quantify the poloidal and toroidal charge-exchange flux.
- Combined with the high energy and time resolution of a LENA, arrays of Pd-MOS devices could provide critical data for edge plasma – neutral model validation.



Pd-MOS H-sensor DiMES head

Continued interest at DIII-D and NSTX to evaluate Pd-MOS H-sensors